## NSN 5961-01-326-2359

Transistor - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-326-2359 **Inclosure Material:** Metal **Overall Length:** 1.260 inches **Overall Height:** Between 0.250 inches and 0.340 inches **Overall Width:** 0.700 inches **Mounting Facility Quantity: Internal Configuration:** Field effect Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-213aa **Electrode Internally-electrically Connected To Case: Mounting Method:** Unthreaded hole **Features Provided:** Burn in and electrostatic sensitive and quality assurance level tx **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 500.0 drain to source voltage and 500.0 drain to gate voltage **Current Rating Per Characteristic:** 6.00 amperes drain current **Power Rating Per Characteristic:** 70.0 watts total power dissipation **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 pin and 1 case **Specification Data:** 81349-mil-s-19500/569 government specification Shelf Life: N/a

No

**Unit Of Measure:** 

**Demilitarization:** 

## **NSN 5961-01-326-2359** Transistor - Page 2 of 2



Fiig:

A110a0